



QPP-008
35W, 925-960MHz
Class AB Driver Stage

QuikPAC Module Data

General description:

The **QPP-008 QuikPAC™** RF power module is an impedance matched Class AB amplifier stage designed for use in the driver stage of linear RF power amplifiers for cellular base stations. The power transistor is fabricated using Xemod's advanced design LDMOS process. The gate terminal is connected directly to the control voltage pin, allowing direct control of the bias. The user must supply the proper value of V_{GS} to set the desired quiescent current.

Features:

- Single Polarity Operation
- Matched for 50 Ω RF interfaces
- XeMOS FET Technology
- Stable Performance
- QuikPAC System Compatible
- QuikClip or Flange Mounting

Standard Operating Conditions

Parameter	Symbol	Min	Nom	Max	Units
Frequency Range	F	925		960	MHz
Supply (Drain) Voltage	V_D	26.0	28.0	32.0	VDC
Bias (Gate) Voltage	V_G	3.0	3.5	5.0	VDC
Bias (Gate) Current, Average	I_G			1.0	mA
RF Source & Load Impedance	Ω		50		Ohms
Load Impedance for Stable Operation (All Phases)	VSWR			10:1	
Operating Baseplate Temperature	T_{OP}	-20		+90	$^{\circ}C$
Output Device Thermal Resistance, Channel to Baseplate	Θ_{jc}		1.9		$^{\circ}C/W$

Maximum Ratings

Parameter	Symbol	Value	Units
Supply (Drain) Voltage	V_{DD}	35	VDC
Control (Gate) Voltage, $V_{DD} = 0$ VDC	V_G	15	VDC
Input RF Power	P_{IN}	2.5	W
Load Impedance for continuous operation without damage	VSWR	3:1	
Output Device Channel Temperature		200	$^{\circ}C$
Lead temperature during reflow soldering		+210	$^{\circ}C$
Storage Temperature	T_{STG}	-40 to +100	$^{\circ}C$

Performance at 28VDC & 25 $^{\circ}C$

Parameter	Symbol	Min	Nom	Max	Units
Supply (Drain) Voltage	$V_{D1,2}$	27.8	28.0	28.2	VDC
Quiescent Current (total)	I_{DQ}	270	300	330	mA
Power Output at 1 dB Compression (single tone)	P_{-1}	35	40		W
Gain at 35W PEP (two tone)	G	13.5	15.5		dB
Gain Variation over frequency at 35W Output (two tone)	ΔG		0.3	0.5	dB
Input Return Loss (50 Ω Ref) at 35W PEP (two tone)	IRL	11.5	17.5		dB
Drain Efficiency at 35W P_{out} (single tone)	η	40	45		%
Drain Efficiency at 35W PEP (two tone)	η	32	36		%
3 rd Order IMD Product (2 tone at 35W PEP; 1 MHz spacing)			-30	-28	dBc

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Performance at 28VDC & 25°C (continued)

Parameter	Symbol	Min	Nom	Max	Units
IMD Variation – 100 kHz to 25 MHz tone spacing			1.0	2.0	dB
2 nd Harmonic at 35W P _{out} (single tone)		-35			dBc
3 rd Harmonic at 35W P _{out} (single tone)		-40			dBc
Electrical Delay	τ_d		3.5		ns
Transmission Phase Flatness			0.5		degrees

Notes:

This QuikPAC module requires an externally supplied gate voltage (V_{GS}) on the gate lead (pin 3) to set the operating point (quiescent current- I_{DQ}) of the power transistor. V_{GS} may be safely set to any voltage in the range listed in the table. This permits a wide range of quiescent current to be used. Since the operating characteristics of the module will vary as I_{DQ} changes, the bias setting will depend on the application. The data provided in the Performance section of this data sheet was obtained with I_{DQ} set to a value within the range listed (a nominal value $\pm 10\%$). This particular value was chosen to optimize gain, IMD performance, and efficiency simultaneously.

Gate voltage must be applied coincident with or after application of the drain voltage to prevent potentially destructive oscillations. Bias voltages should never be applied to a module unless it is terminated on both input and output.

The V_{GS} corresponding to a specific I_{DQ} will vary from module to module. This is due to the normal die-to-die variation in threshold voltage of LDMOS transistors.

Since the gate bias of an LDMOS transistor changes with device temperature, it may be necessary to use a V_{GS} supply with thermal compensation if operation over a wide temperature range is required.

Internal RF decoupling is included on all bias leads. No additional bypass elements are required, however some applications may require energy storage on the drain leads to accommodate time-varying waveforms.

The RF leads are internally protected against DC voltages up to 100V. Care should be taken to avoid video transients that may damage the active devices.

Package Styles

This model is available in the A1F (H10890) package style, shown here for reference. Please see the applicable outline drawing for detailed dimensions.

